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U. S. PATENT DOCUMENTS

*	DOCUMENT NUMBER	DATE	NAME	CLASS*	SUB-CLASS*	FILING DATE IF APPRO.
41	5 7 2 5 6 7 4	3/10/98	Moustakas et al.	—	—	
	6 0 5 1 8 4 9	4/18/00	Davis et al.	—	—	
	5 8 5 8 8 6 2	1/12/99	Westwater et al.	—	—	
	5 9 6 2 8 6 3	10/5/99	Russell et al.	—	—	
	5 3 8 1 7 5 3	1/17/95	Okajima et al.	—	—	
	6 0 6 3 2 4 6	5/16/00	Wolfe et al.	—	—	
	4 8 8 6 6 8 3	12/12/89	Hoke et al.	—	—	
	5 3 3 4 2 9 6	8/2/94	Henkens et al.	—	—	
	6 0 3 3 8 6 6	3/7/00	Guo et al.	—	—	
41	5 9 2 2 1 8 3	7/13/99	Rauth	—	—	

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41	2 0 8 6 1 2 1	3/27/90	Japan	Nishibe Toru et al.	—	—	
41	1 1 1 7 7 1 3 4	7/2/99	Japan	Yamada Takeshi	—	—	

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Publication No. WO026422A1 for "HIGH PURITY GALLIUM FOR PREPARATION OF COMPOUND SEMICONDUCTOR, AND METHOD AND APPARATUS FOR PURIFYING THE SAME" by Yamamura et al., published on May 11, 2000;

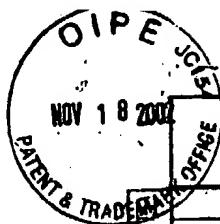
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J. Westwater, D.P. Gosain, S. Tomyia, S. Usui, and H. Ruda "GROWTH OF SILICON NANOWIRES VIA GOLD/SILANE VAPOR-LIQUID-SOLID REACTION", J. Vac. Sci. Technol. B 15(3), May/June 1997, 554-557;

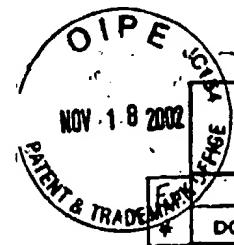
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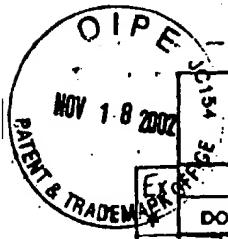
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